

isc Silicon NPN Power Transistors

TIP41

DESCRIPTION

- DC Current Gain -h_{FE} = 30(Min)@ I_C= 0.3A
- Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)} = 40V(Min)
- Complement to Type TIP42
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Designed for use in general purpose amplifer and switching applications

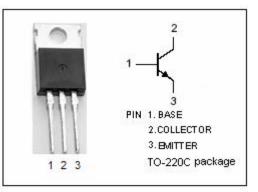
ABSOLUTE	MAXIMUM RATING	GS(T₂=25℃)
ADOOLOIL		

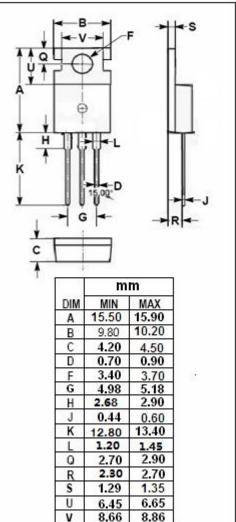
SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	40	V	
V _{CEO}	Collector-Emitter Voltage	40	V	
V_{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	6	А	
Ісм	Collector Current-Peak	10	А	
I _B	Base Current	2	А	
Pc	Collector Power Dissipation Tc=25°C	65	W	
	Collector Power Dissipation T _a =25°C	2		
Tj	Junction Temperature	150	°C	
T _{stg}	Storage Temperature Range	-65~150	°C	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.67	°C/W
Rth j-a	Thermal Resistance, Junction to Ambient	57	°C/W

1





isc website: <u>www.iscsemi.com</u>



isc Silicon NPN Power Transistors

TIP41

ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V _{CEO} (SUS)	Collector-Emitter Sustaining Voltage	I _C = 30mA; I _B = 0	40		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.6A		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 6A; V _{CE} = 4V		2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0		0.4	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 40V; I _B = 0		0.7	mA
І _{ЕВО}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		1.0	mA
h _{FE-1}	DC Current Gain	I _C = 0.3A ; V _{CE} = 4V	30		
h _{FE-2}	DC Current Gain	I _C = 3A ; V _{CE} = 4V	15	75	
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A ; V _{CE} = 10V	3		MHz

Switching Time

t _{on}	Turn-On Time	I _C = 6A; I _{B1} = -I _{B2} = 0.6A; V _{BE(off)} = 4V, R _L = 5 Ω	0.6	μ S
t _{off}	Turn-Off Time		1.0	μ S

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and *isc website:* <u>www.iscsemi.com</u> ² *isc* & *iscsemi* is registered trademark



INCHANGE SEMICONDUCTOR

specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

3